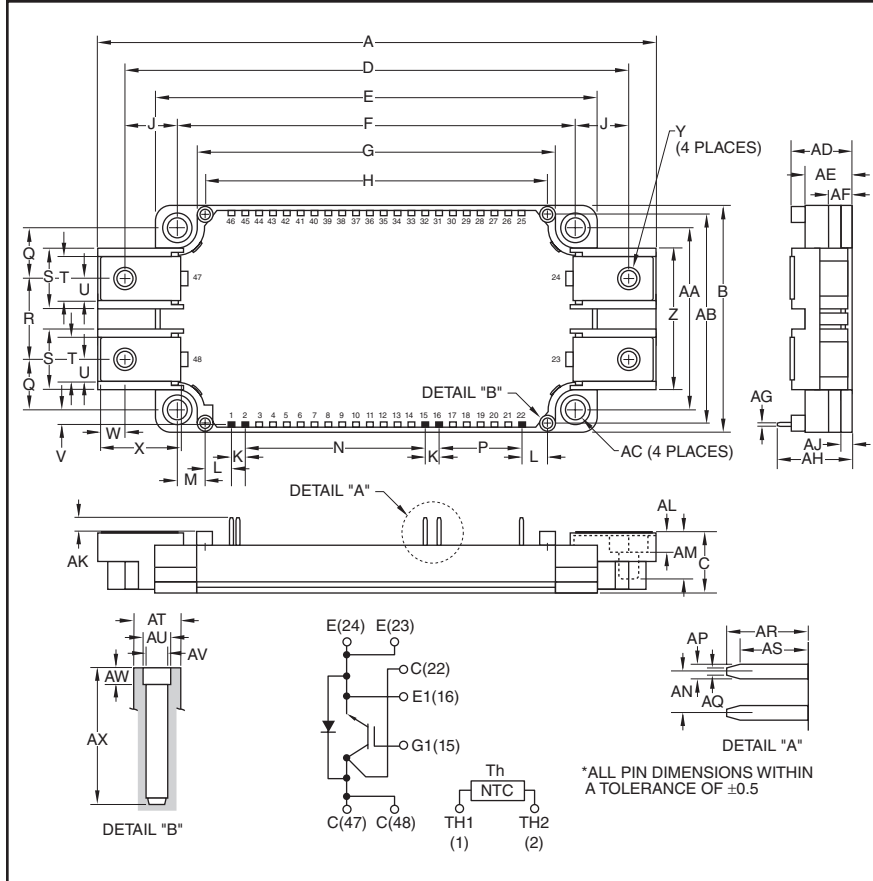


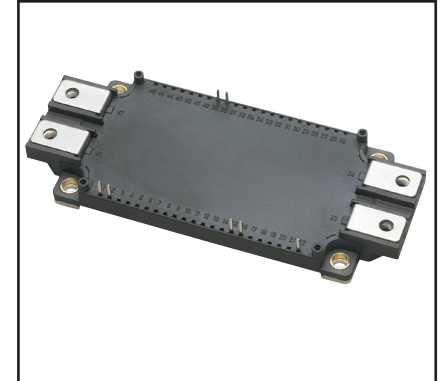
### Single IGBTMOD™ NX-Series Module 600 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.98	152.0
B	2.44	62.0
C	0.67	17.0
D	5.39	137.0
E	4.79	121.7
F	4.33±0.02	110.0±0.5
G	3.89	99.0
H	3.72	94.5
J	0.53	13.5
K	0.15	3.8
L	0.28	7.25
M	0.30	7.75
N	1.95	49.54
P	0.9	22.86
Q	0.55	14.0
R	0.87	22.0
S	0.67	17.0
T	0.48	12.0
U	0.24	6.0
V	0.16	4.2
W	0.37	6.5
X	0.83	21.14
Y	M6	M6

Dimensions	Inches	Millimeters
Z	1.53	39.0
AA	1.97±0.02	50.0±0.5
AB	2.26	57.5
AC	0.22 Dia.	5.5 Dia.
AD	0.67+0.04/-0.02	17.0+1.0/-0.5
AE	0.51	13.0
AF	0.27	7.0
AG	0.03	0.8
AH	0.81	20.5
AJ	0.12	3.0
AK	0.14	3.5
AL	0.21	5.4
AM	0.49	12.5
AN	0.15	3.81
AP	0.05	1.15
AQ	0.025	0.65
AR	0.29	7.4
AS	0.24	6.2
AT	0.17 Dia.	4.3 Dia.
AU	0.10 Dia.	2.5 Dia.
AV	0.08 Dia.	2.1 Dia.
AW	0.06	1.5
AX	0.49	12.5



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration with a reverse connected rectifier grade free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Rectifier Grade Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- Motion/Servo Control
- Photovoltaic/Fuel Cell

#### Ordering Information:

Example: Select the complete module number you desire from the table below -i.e. QIS1260015 is a 1200V ( $V_{CES}$ ), 600 Ampere Single IGBTMOD™ Power Module.

**QIS1260015**  
**Single IGBTMOD™ NX-Series Module**  
 600 Amperes/1200 Volts

**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

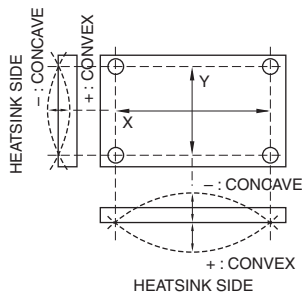
Characteristics	Symbol	QIS1260015	Units
Power Device Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Mounting Torque, M5 Mounting Screws	—	31	in-lb
Mounting Torque, M6 Main Terminal Screws	—	40	in-lb
Module Weight (Typical)	—	330	Grams
Baseplate Flatness, On Centerline X, Y (See Below)	—	$\pm 0 \sim +100$	$\mu\text{m}$
Isolation Voltage (Terminals to Baseplate, $f = 60\text{Hz}$ , AC 1 minute)	$V_{ISO}$	2500	Volts

**Inverter Sector**

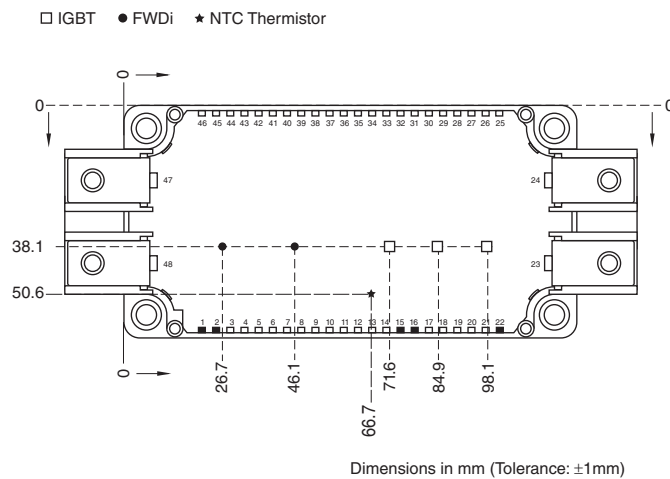
Collector-Emitter Voltage ( $V_{GE} = 0\text{V}$ )	$V_{CES}$	1200	Volts
Gate-Emitter Voltage ( $V_{CE} = 0\text{V}$ )	$V_{GES}$	$\pm 20$	Volts
Collector Current (DC, $T_C = 90^\circ\text{C}$ ) <sup>*1,*5,*9</sup>	$I_C$	600	Amperes
Peak Collector Current (Pulse) <sup>*4</sup>	$I_{CM}$	1200	Amperes
Maximum Collector Dissipation ( $T_C = 25^\circ\text{C}$ ) <sup>*1,*5</sup>	$P_C$	3785	Watts
Emitter Current ( $T_C = 25^\circ\text{C}$ ) <sup>*1,*5,*9</sup>	$I_E^{*3}$	600	Amperes
Peak Emitter Current (Pulse) <sup>*4</sup>	$I_{EM}^{*3}$	1200	Amperes

\*1 Case temperature ( $T_C$ ) and heatsink temperature ( $T_f$ ) measured point is just under the chips.  
 \*3 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).  
 \*4 Pulse width and repetition rate should be such that device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.  
 \*5 Junction temperature ( $T_j$ ) should not increase beyond maximum junction temperature ( $T_{j(max)}$ ) rating.  
 \*9 Use both of each main terminal (collector and emitter) to connect external wiring.

**BASEPLATE FLATNESS MEASUREMENT POINT**



**CHIP LOCATION (TOP VIEW)**



**QIS1260015**  
**Single IGBTMOD™ NX-Series Module**  
 600 Amperes/1200 Volts

**Electrical and Mechanical Characteristics, T<sub>j</sub> = 25°C unless otherwise specified**

**Inverter Sector**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Collector Cutoff Current	I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	—	—	1.0	mA	
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	I <sub>C</sub> = 60mA, V <sub>CE</sub> = 10V	6	7	8	Volts	
Gate Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	—	—	0.5	μA	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C* <sup>6</sup>	—	2.0	2.6	Volts	
		I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 125°C* <sup>6</sup>	—	2.2	—	Volts	
		I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 150°C* <sup>6</sup>	—	1.9	—	Volts	
Input Capacitance	C <sub>ies</sub>		—	—	100	nF	
Output Capacitance	C <sub>oes</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V	—	—	9.0	nF	
Reverse Transfer Capacitance	C <sub>res</sub>		—	—	2.0	nF	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V	—	3000	—	nC	
Inductive	Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A,		—	660	ns
	Turn-on Rise Time	t <sub>r</sub>	V <sub>GE</sub> = ±15V,		—	190	ns
Switch	Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 2.2Ω, I <sub>E</sub> = 600A,		—	700	ns
	Turn-off Fall Time	t <sub>f</sub>	Inductive Loas Switching Operation		—	600	ns
Emitter-Collector Voltage	V <sub>EC</sub> <sup>*3</sup>	I <sub>E</sub> = 600A, V <sub>GE</sub> = 0V, T <sub>j</sub> = 25°C* <sup>6</sup>	—	1.0	1.2	Volts	
		I <sub>E</sub> = 600A, V <sub>GE</sub> = 0V, T <sub>j</sub> = 125°C* <sup>6</sup>	—	0.9	1.1	Volts	

**Thermal and Mechanical Characteristics, T<sub>j</sub> = 25°C unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Module Lead Resistance	R <sub>lead</sub>	Main Terminals-Chip (Per Switch)	—	0.6	—	mΩ
Thermal Resistance, Junction to Case* <sup>1</sup>	R <sub>th(j-c)Q</sub>	Per IGBT	—	—	0.033	°C/W
Thermal Resistance, Junction to Case* <sup>1</sup>	R <sub>th(j-c)D</sub>	Per FWDi	—	—	0.028	°C/W
Contact Thermal Resistance* <sup>1</sup> (Case to Heatsink)	R <sub>th(c-f)</sub>	Thermal Grease Applied (Per 1 Module)* <sup>2</sup>	—	0.015	—	°C/W
Internal Gate Resistance	R <sub>Gint</sub>	T <sub>C</sub> = 25°C	0.7	1.0	1.3	Ω
		T <sub>C</sub> = 125°C	1.4	2.0	2.6	Ω
External Gate Resistance	R <sub>G</sub>		1.0	—	10	Ω

**NTC Thermistor Sector, T<sub>j</sub> = 25°C unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Zero Power Resistance	R	T <sub>C</sub> = 25°C	4.85	5.00	5.15	kΩ
Deviation of Resistance	ΔR/R	T <sub>C</sub> = 100°C, R <sub>100</sub> = 493Ω	-7.3	—	+7.8	%
B Constant	B <sub>(25/50)</sub>	Approximate by Equation* <sup>9</sup>	—	3375	—	K
Power Dissipation	P <sub>25</sub>	T <sub>C</sub> = 25°C	—	—	10	mW

\*1 Case temperature (T<sub>C</sub>) and heatsink temperature (T<sub>H</sub>) measured point is just under the chips.

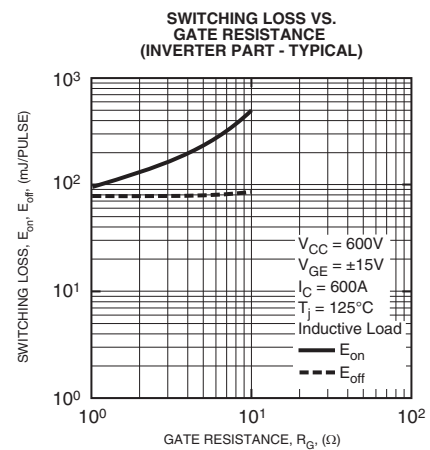
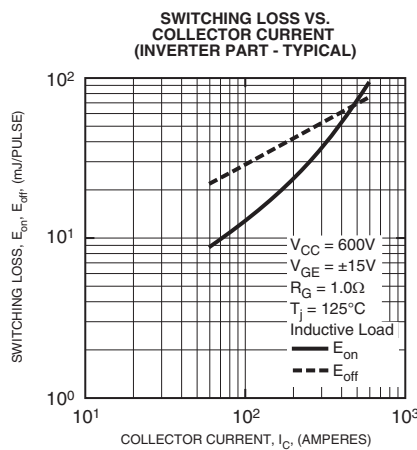
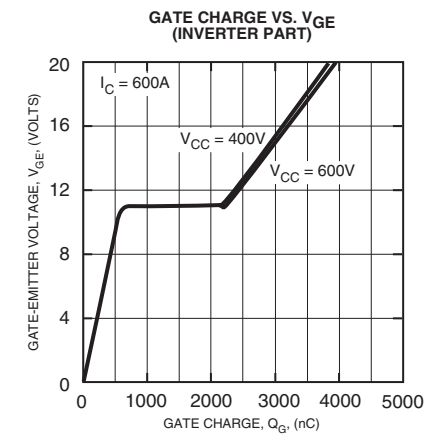
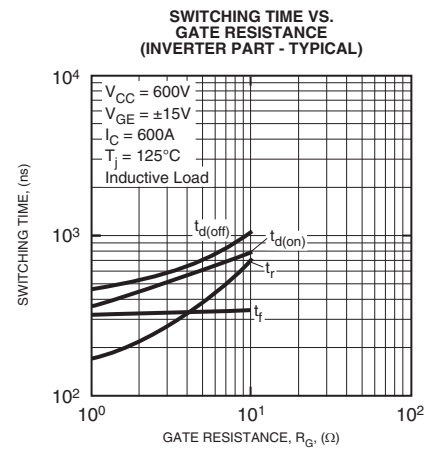
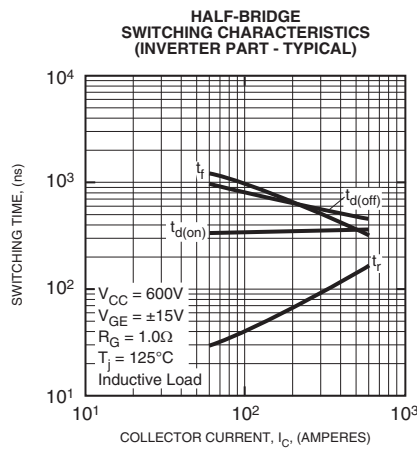
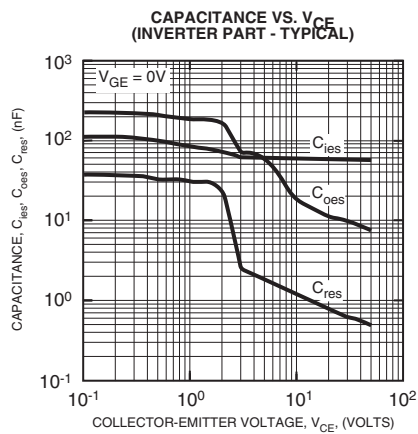
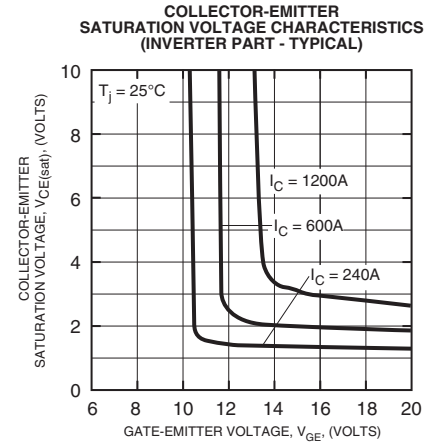
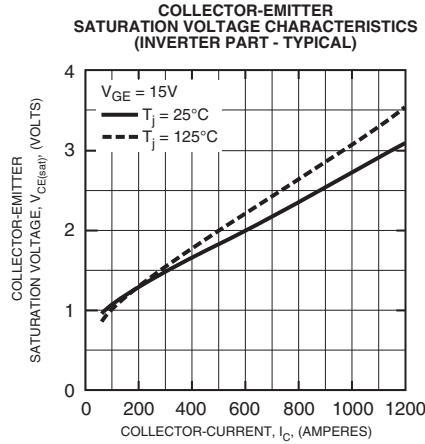
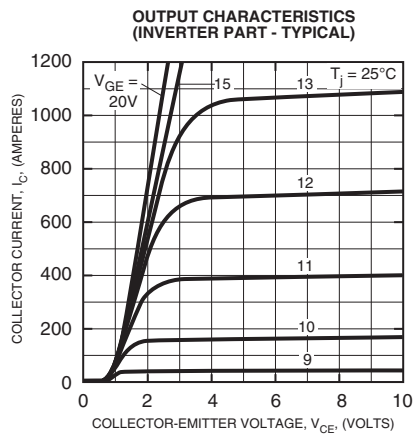
\*2 Typical value is measured by using thermally conductive grease of λ = 0.9 [W/(m • K)].

\*3 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).

\*6 Pulse width and repetition rate should be such as to cause negligible temperature rise.

\*9  $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$  R<sub>25</sub>: Resistance at Absolute Temperature T<sub>25</sub> [K], R<sub>50</sub>: resistance at Absolute Temperature T<sub>50</sub> [K],  
 T<sub>25</sub> = 25 [°C] + 273.15 = 298.15 [K], T<sub>50</sub> = 50 [°C] + 273.15 = 323.15 [K]

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**Single IGBTMOD™ NX-Series Module**  
 600 Amperes/1200 Volts



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